Controllable Synthesis of 2D Perovskite on Different Substrates and Its Application as Photodetector

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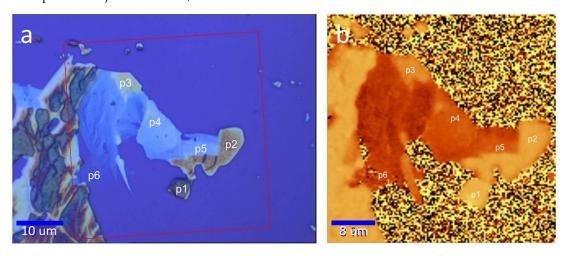


Figure S1. (a) CH₃NH₃PbI₃ perovskite with different thicknesses marked by p1 to p6. The thickness of P1 to P6 is measured to be 63 nm, 41 nm, 25 nm, 18 nm, 11 nm, 2 nm, respectively. (b) The corresponding PL mapping images of the CH₃NH₃PbI₃ perovskite acquired in the red square in (a).

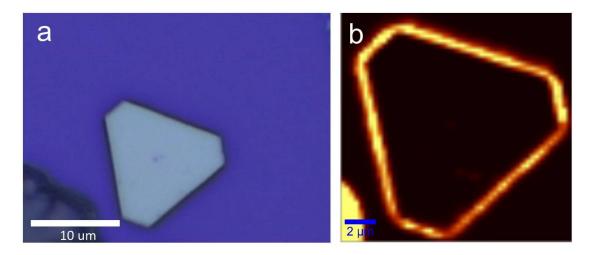


Figure S2. (a) Optical microscopy image of the converted CH₃NH₃PbI₃ perovskite without supplying sufficient CH₃NH₃I molecules during the conversion process on SiO₂/Si substrate. (b) PL mapping image of the converted CH₃NH₃PbI₃ perovskite in (a).

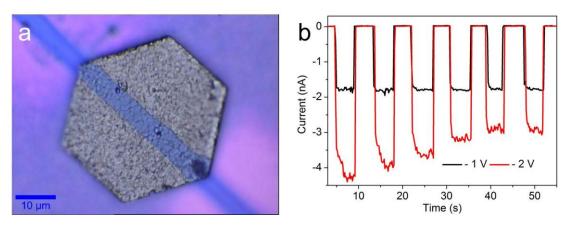


Figure S3. (a) Optical microscopy image of a 2D CH $_3$ NH $_3$ PbI $_3$ platelet phototransistor. (b) Time-dependent photocurrent of the 2D CH $_3$ NH $_3$ PbI $_3$ platelet phototransistor during the laser switching on/off process under negative source–drain voltages V $_{sd}$ of -1 and -2 V.